

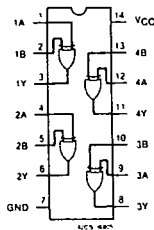
**CD54/74HC86  
CD54/74HCT86**

T-43-21-00

**High-Speed CMOS Logic**

HARRIS SEMICONDUCTOR

27E D ■ 4302271 0017532 2 ■ HAS



**FUNCTIONAL DIAGRAM AND  
TERMINAL ASSIGNMENT**

**Quad 2 - Input EXCLUSIVE - OR Gate**

**Type Features:**

- Four independent EXCLUSIVE - OR gates
- Buffered inputs and outputs

**Applications:**

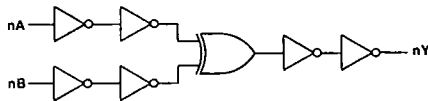
- Logical comparators
- Parity generators and checkers
- Adders/Subtractors

The RCA CD54/74HC86 and CD54/74HCT86 contain four independent EXCLUSIVE-OR gates in one package. They provide the system designer with a means for implementation of the EXCLUSIVE-OR function.

The CD54HC/HCT86 are supplied in 14-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT86 are supplied in 14-lead plastic dual-in-line packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

**Family Features:**

- Fanout (Over Temperature Range):  
Standard Outputs - 10 LSTTL Loads  
Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range:  
CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:  
2 to 6 V Operation  
High Noise Immunity:  $N_{IL} = 30\%$ ,  $N_{IH} = 30\%$  of  $V_{CC}$   
@  $V_{CC} = 5 V$
- CD54HCT/CD74HCT Types:  
4.5 to 5.5 V Operation  
Direct LSTTL Input Logic Compatibility  
 $V_{IL} = 0.8 V$  Max.,  $V_{IH} = 2 V$  Min.  
CMOS Input Compatibility  
 $I_i \leq 1 \mu A$  @  $V_{OL}$ ,  $V_{OH}$



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Fig. 1 - Logic diagram each gate.

**TRUTH TABLE**

INPUTS		OUTPUT
nA	nB	nY
L	L	L
L	H	H
H	L	H
H	H	L

H = HIGH voltage level.  
L = LOW voltage level.

**CD54/74HC86**  
**CD54/74HCT86**

**MAXIMUM RATINGS, Absolute-Maximum Values:**

DC SUPPLY-VOLTAGE, (V <sub>cc</sub> ): (Voltages referenced to ground)	-0.5 to +7 V
DC INPUT DIODE CURRENT, I <sub>ik</sub> (FOR V <sub>i</sub> < -0.5 V OR V <sub>i</sub> > V <sub>cc</sub> + 0.5 V)	±20 mA
DC OUTPUT DIODE CURRENT, I <sub>ok</sub> (FOR V <sub>o</sub> < -0.5 V OR V <sub>o</sub> > V <sub>cc</sub> + 0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I <sub>o</sub> ) (FOR -0.5 V < V <sub>o</sub> < V <sub>cc</sub> + 0.5 V)	±25 mA
DC V <sub>cc</sub> OR GROUND CURRENT (I <sub>cc</sub> ):	±50 mA
POWER DISSIPATION PER PACKAGE (P <sub>o</sub> ):	
For T <sub>A</sub> = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T <sub>A</sub> = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T <sub>A</sub> = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T <sub>A</sub> = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T <sub>A</sub> = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T <sub>A</sub> = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T <sub>A</sub> ):	
PACKAGE TYPE F, H	-55 to +125°C
PACKAGE TYPE E, M	-40 to +85°C
STORAGE TEMPERATURE (T <sub>stg</sub> ):	-65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 ± 1/32 in. (1.59 ± 0.79 mm) from case for 10 s max.	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) with solder contacting lead tips only	+300°C

**RECOMMENDED OPERATING CONDITIONS:**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T <sub>A</sub> = Full Package-Temperature Range) V <sub>cc</sub> .*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V <sub>i</sub> , V <sub>o</sub>	0	V <sub>cc</sub>	V
Operating Temperature T <sub>A</sub> :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t <sub>r</sub> , t <sub>f</sub>			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

\*Unless otherwise specified, all voltages are referenced to Ground.

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**CD54/74HC86**  
**CD54/74HCT86**

STATIC ELECTRICAL CHARACTERISTICS

T-43-21

CHARACTERISTICS	CD74HC86/CD54HC86										CD74HCT86/CD54HCT86								UNITS		
	TEST CONDITIONS			74HC/54HC TYPE			74HC TYPE		54HC TYPE		TEST CONDITIONS		74HCT/54HCT TYPE			74HCT TYPE		54HCT TYPE			
	V <sub>I</sub> V	I <sub>O</sub> mA	V <sub>CC</sub> V	+25°C			-40/ +85°C		-55/ +125°C		V <sub>I</sub> V	V <sub>CC</sub> V	+25°C			-40/ +85°C		-55/ +125°C			
				Min	Typ	Max	Min	Max	Min	Max			Min	Typ	Max	Min	Max	Min		Max	
High-Level Input Voltage	V <sub>IH</sub>		2	1.5	—	—	1.5	—	1.5	—	—	4.5	2	—	—	2	—	2	—	V	
			4.5	3.15	—	—	3.15	—	3.15	—	—	5.5									
			6	4.2	—	—	4.2	—	4.2	—											
Low-Level Input Voltage	V <sub>IL</sub>		2	—	—	0.5	—	0.5	—	0.5	—	4.5	—	—	0.8	—	0.8	—	0.8	V	
			4.5	—	—	1.35	—	1.35	—	1.35	—	5.5	—	—	0.8	—	0.8	—	0.8		
			6	—	—	1.8	—	1.8	—	1.8	—										
High-Level Output Voltage	V <sub>OH</sub>	V <sub>IL</sub> or -0.02	2	1.9	—	—	1.9	—	1.9	—	V <sub>IL</sub> or 4.5	4.5	4.4	—	—	4.4	—	4.4	—	V	
CMOS Loads	V <sub>IH</sub>		6	5.9	—	—	5.9	—	5.9	—	V <sub>IH</sub>										
TTL Loads	V <sub>IL</sub> or V <sub>IH</sub>		4	4.5	3.98	—	—	3.84	—	3.7	—	V <sub>IL</sub> or 4.5	3.98	—	—	3.84	—	3.7	—	V	
			5.2	6	5.48	—	—	5.34	—	5.2	—	V <sub>IH</sub>									
Low-Level Output Voltage	V <sub>OL</sub>	V <sub>IL</sub> or 0.02	2	—	—	0.1	—	0.1	—	0.1	V <sub>IL</sub> or 4.5	4.5	—	—	0.1	—	0.1	—	0.1	V	
CMOS Loads	V <sub>IH</sub>		6	—	—	0.1	—	0.1	—	0.1	V <sub>IH</sub>										
TTL Loads	V <sub>IL</sub> or V <sub>IH</sub>		4	4.5	—	—	0.26	—	0.33	—	0.4	V <sub>IL</sub> or 4.5	—	—	0.26	—	0.33	—	0.4	V	
			5.2	6	—	—	0.26	—	0.33	—	0.4	V <sub>IH</sub>									
Input Leakage Current	I <sub>I</sub>	V <sub>CC</sub> or Gnd	6	—	—	±0.1	—	±1	—	±1	Any Voltage Between V <sub>CC</sub> and Gnd	5.5	—	—	±0.1	—	±1	—	±1	µA	
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or Gnd	0	6	—	—	2	—	20	—	40	V <sub>CC</sub> or Gnd	5.5	—	—	2	—	20	—	40	µA
Additional Quiescent Device Current per Input Pin: 1 Unit Load	ΔI <sub>CC</sub> *										V <sub>CC</sub> -2.1	4.5 to 5.5	—	100	360	—	450	—	490	µA	

\*For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4 V, V<sub>CC</sub> = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
All Inputs	1

\* Unit load is ΔI<sub>CC</sub> limit specified in Static Characteristic Chart, e.g., 360 µA max. @ 25°C.

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**CD54/74HC86**  
**CD54/74HCT86**

SWITCHING CHARACTERISTICS ( $V_{CC} = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$ , Input  $t_r, t_f = 6\text{ ns}$ )

CHARACTERISTIC	$C_L$ pF	SYMBOL	TYPICAL VALUES		UNITS
			54/74HC	54/74HCT	
Propagation Delay, Any Input	15	$t_{PLH}$ $t_{PHL}$	9	13	ns
Power Dissipation Capacitance*	—	$C_{PD}$	22	27	pF

\*  $C_{PD}$  is used to determine the dynamic power consumption, per gate.

$P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where:

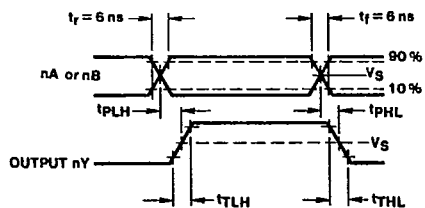
$f_i$  = input frequency.

$C_L$  = output load capacitance.

$V_{CC}$  = supply voltage.

SWITCHING CHARACTERISTICS ( $C_L = 50\text{ pF}$ , Input  $t_r, t_f = 6\text{ ns}$ )

CHARACTERISTIC	SYMBOL	$V_{CC}$	25°C				-40°C to +85°C				-55°C to +125°C				UNITS
			HC		HCT		74HC		74HCT		54HC		54HCT		
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay, nA, nB to nY	$t_{PLH}$	2	—	120	—	—	150	—	—	180	—	—	—	ns	
	$t_{PHL}$	4.5	24	—	32	—	30	—	40	—	36	—	48		
		6	20	—	—	—	26	—	—	—	31	—	—		
Output Transition Time	$t_{TLH}$	2	—	75	—	—	95	—	—	110	—	—	ns		
	$t_{THL}$	4.5	15	—	15	—	19	—	19	—	22	—		22	
		6	13	—	—	—	16	—	—	—	19	—		—	
Input Capacitance	$C_i$	—	—	10	—	10	—	10	—	10	—	10	pF		



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	54/74HC	54/74HCT
Input Level	$V_{CC}$	3 V
Switching Voltage, $V_S$	50% $V_{CC}$	1.3 V

Fig. 2 - Transition times and propagation delay times.

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